

# Andreas Lesnik

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5559312/publications.pdf>

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11  
papers

272  
citations

1163117

8  
h-index

1281871

11  
g-index

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all docs

11  
docs citations

11  
times ranked

441  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Methodology for the investigation of threading dislocations as a source of vertical leakage in AlGaIn/GaN-HEMT heterostructures for power devices. Journal of Applied Physics, 2019, 125, .                                    | 2.5 | 30        |
| 2  | Two charge states of the $C_N$ acceptor in GaN: Evidence from photoluminescence. Physical Review B, 2018, 98, .  | 3.2 | 84        |
| 3  | Twin domain imaging in topological insulator $Bi_2Te_3$ and $Bi_2Se_3$ epitaxial thin films by scanning X-ray nanobeam microscopy and electron backscatter diffraction. Journal of Applied Crystallography, 2017, 50, 369-377. | 4.5 | 28        |
| 4  | Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. Applied Physics Letters, 2017, 110, .   | 3.3 | 6         |
| 5  | Properties of $C_d$ -doped GaN. Physica Status Solidi (B): Basic Research, 2017, 254, 1600708.   | 1.5 | 33        |
| 6  | Leakage currents and Fermi-level shifts in GaN layers upon iron and carbon-doping. Journal of Applied Physics, 2017, 122, .  | 2.5 | 23        |
| 7  | On reduction of current leakage in GaN by carbon-doping. Applied Physics Letters, 2016, 109, .   | 3.3 | 25        |
| 8  | Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. Journal of Crystal Growth, 2016, 440, 6-12.  | 1.5 | 11        |
| 9  | Enhanced sheet carrier densities in polarization controlled AlInN/AlN/GaN/InGaIn field-effect transistor on Si (111). AIP Advances, 2015, 5, .   | 1.3 | 4         |
| 10 | Growth of AlInN/GaN distributed Bragg reflectors with improved interface quality. Journal of Crystal Growth, 2015, 414, 105-109.   | 1.5 | 22        |
| 11 | Characterization of AlInN/AlN/GaN FET structures using x-ray diffraction, x-ray reflectometry and grazing incidence x-ray fluorescence analysis. Journal Physics D: Applied Physics, 2014, 47, 355106.                         | 2.8 | 6         |